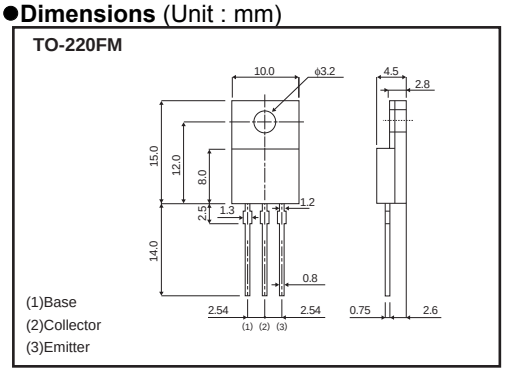
10V Drive Nch MOSFET

R5005CNX

●Structure
Silicon N-channel MOSFET

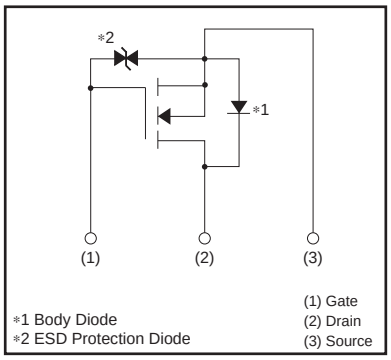
●Features
1) Low on-resistance.
2) Fast switching speed.
3) Gate-source voltage (V_{GSS}) guaranteed to be ±30V.
4) Drive circuits can be simple.
5) Parallel use is easy.

●Dimensions (Unit : mm)



●Applications
Switching

●Inner circuit



●Packaging specifications

Type	Package	Bulk
	Basic ordering unit (pieces)	500pcs

●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	500	V
Gate-source voltage		V_{GSS}	±30	V
Drain current	Continuous	I_D *3	±5	A
	Pulsed	I_{DP} *1	±20	A
Source current (Body Diode)	Continuous	I_S *3	5	A
	Pulsed	I_{SP} *1	20	A
Avalanche current		I_{AS} *2	2.5	A
Avalanche energy		E_{AS} *2	1.6	mJ
Total power dissipation (Tc=25°C)		P_D	40	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%
*2 L≒500μH, V_{DD}=50V, R_G=25Ω, Starting, Tch=25°C
*3 Limited only by maximum temperature allowed

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	3.13	°C/W

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	V_{GS}=±30V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	500	–	–	V	I_D=1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	100	μA	V_{DS}=500V, V_{GS}=0V
Gate threshold voltage	$V_{GS(th)}$	2.5	–	4.5	V	V_{DS}=10V, I_D=1mA
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	1.3	1.6	Ω	I_D=2.5A, V_{GS}=10V
Forward transfer admittance	$\|Y_{fs}\|$ *	1.5	–	–	S	I_D=2.5A, V_{DS}=10V
Input capacitance	C_{iss}	–	320	–	pF	V_{DS}=25V
Output capacitance	C_{oss}	–	180	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	15	–	pF	f=1MHz
Turn-on delay time	$t_{d(on)}$ *	–	20	–	ns	I_D=2.5A, V_{DD}≒250V
Rise time	t_r *	–	25	–	ns	V_{GS}=10V
Turn-off delay time	$t_{d(off)}$ *	–	40	–	ns	R_L=100Ω
Fall time	t_f *	–	20	–	ns	R_G=10Ω
Total gate charge	Q_g *	–	10.8	–	nC	V_{DD}≒250V I_D=5A V_{GS}=10V R_L=50Ω / R_G=10Ω
Gate-source charge	Q_{gs} *	–	3.2	–	nC	
Gate-drain charge	Q_{gd} *	–	4.4	–	nC	

* Pulsed

●**Body diode characteristics** (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD} *	–	–	1.5	V	I_S= 5A, V_{GS}=0V

* Pulsed

●**Measurement circuit**

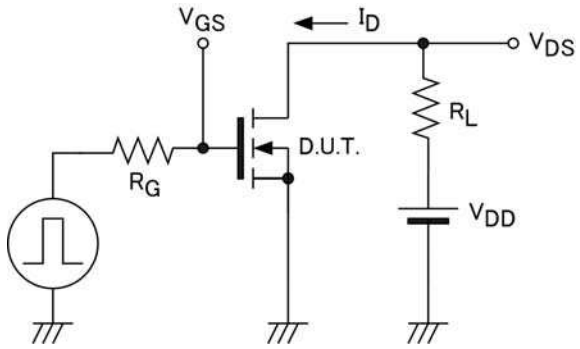


Fig.1 Switching time measurement circuit

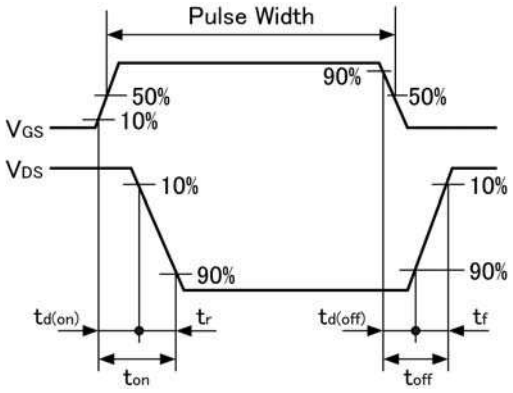


Fig.2 Switching waveforms

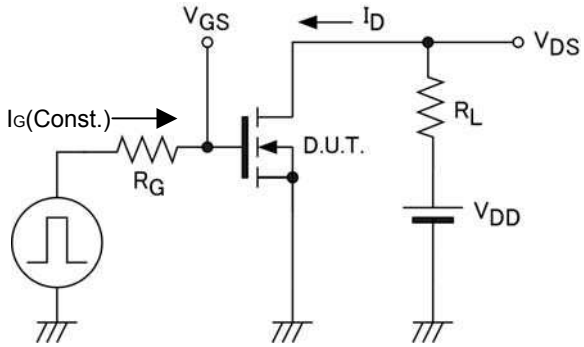


Fig.3 Gate charge measurement circuit

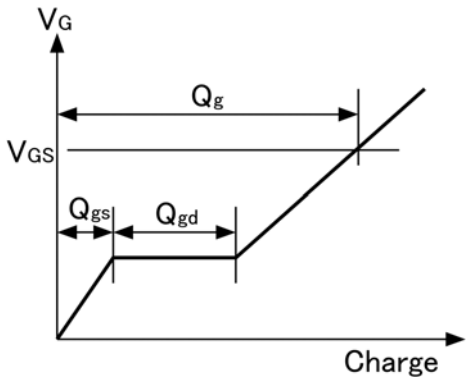


Fig.4 Gate charge waveform

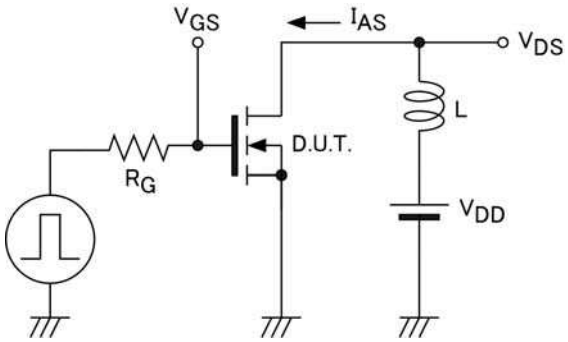


Fig.5 Avalanche measurement circuit

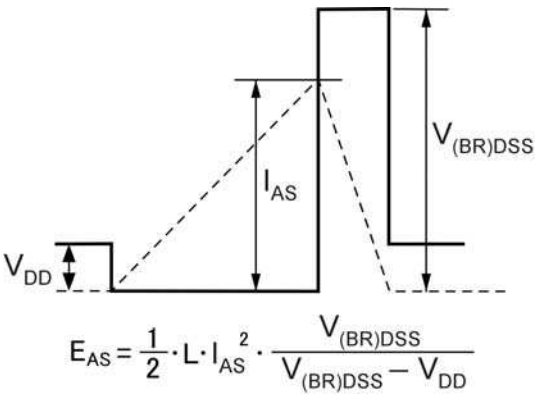


Fig.6 Avalanche waveform

Notes

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